

⌚ Pending

 Active

- L1: (188207) reference adj2 (level or voltage)
- L2: (6459) read adj error
- L3: (63) 1 same 2
- L4: (20) 365/ and 3
- L5: (43) 3 not 4
- L6: (12873) reference adj2 cell
- L7: (33) 2 same 6
- L9: (594) 1 and 2
- L10: (143) 2 and 6
- L11: (1495) 365/185.03
- L12: (874) 365/185.2
- L13: (5966) 365/201
- L14: (2106) 365/210
- L15: (27) 9 and 11
- L17: (28) 9 and 13
- L18: (17) 9 and 14
- L16: (30) 9 and 12
- L19: (232) 9 and 365/
- L20: (164) 19 not (15 or 16 or 17 or 18)
- L21: (46) (COHEN adj2 GUY): in.

 Failed

 Saved

USPAT-US-POPUL-EPD-JPO-DERWENT-ISM-TDS

Default operator: OP

P Pursh

P Highlight all hits are ready

Back Forward Home Stop HTML

| | U | 1 | Document ID | Issue Date | Inventor | Current OR | Current XRef | Retrieval Cla | Title |
|---|---|---|---------------|------------|----------------------------|------------|----------------------------|---------------|---|
| 1 | | | US 6639237 B2 | 20031028 | Takano, Yoshinori et al. | 365/185.22 | 365/185.2; 365/185.21; | | Non-volatile semiconductor device |
| 2 | | | US 6044019 A | 20000328 | Cernea, Raul-Adrian et al. | 365/185.21 | 365/185.2; 365/189.07; | | Non-volatile memory with sensing and method thereof |
| 3 | | | US 5626601 A | 19981027 | Hollmer, Shane C. et al. | 365/185.2 | 365/185.22; 365/185.24; | | Programmed reference |
| 4 | | | US 5605500 A | 19980908 | Campardo, Giovanni et al. | 365/185.2 | 365/185.21 | | Circuit and method for generating read reference signal for non-volatile memory devices |
| 5 | | | US 5057332 A | 19970812 | Audclair, Daniel L. et al. | 714/783 | 365/184; 365/189.07; | | Soft errors handling in EEPROM devices |